



N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
60	0.019 at V _{GS} = 10 V	10		
	0.028 at V _{GS} = 4.5 V	8.2		

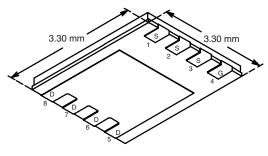
FEATURES

- Halogen-free Option Available
- TrenchFET® Power MOSFET
- New Low Thermal Resistance



100 % R_g Tested



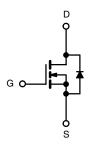


Bottom View

Ordering Information: Si7120DN-T1-E3 (Lead (Pb)-free) Si7120DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

- Primary Side Switch
- Synchronous Rectification



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS \top_{μ}	$_{\lambda}$ = 25 °C, unles	ss otherwise n	oted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	60		V	
Gate-Source Voltage		V _{GS}	± 20		V	
Continuous Drain Current /T 150 °C\a	T _A = 25 °C	- I _D	10	6.3		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		8.0	5.1		
Pulsed Drain Current		I _{DM}	40		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	3.2	1.3		
Single Avalanche Current	L = 0.1 mH	I _{AS}	22 24			
Single Avalanche Energy		E _{AS}			mJ	
Mariana Disabatian	T _A = 25 °C	- P _D	3.8	1.5	W	
Maximum Power Dissipation ^a	T _A = 70 °C		2.4	1.0	۷V	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150			
Soldering Recommendations (Peak Temperature)b, c			260		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifesture Instantanta Ambienti	t ≤ 10 s	R _{thJA}	26	33	°C/W
Maximum Junction-to-Ambient ^a	Steady State		65	81	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.9	2.4	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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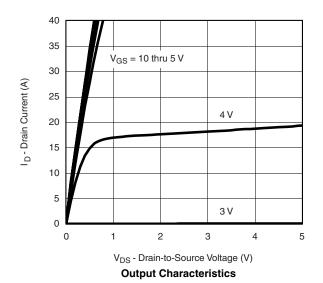
MOSFET SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2.5	3.5	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA		
Zava Cata Valtaga Dvain Current		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			1	μΑ		
Zero Gate Voltage Drain Current	I _{DSS}				5			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α		
	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A	0.015		0.019	Ω		
Drain-Source On-State Resistance ^a		V _{GS} = 4.5 V, I _D = 8.2 A 0.		0.023	0.028			
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		35		S		
Diode Forward Voltage ^a	V_{SD}	I _S = 3.2 A, V _{GS} = 0 V		0.78	1.2	V		
Dynamic ^b				•				
Total Gate Charge	Q_g			30	45			
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$		6.9		nC		
Gate-Drain Charge	Q_{gd}			5.8				
Gate Resistance	R_{g}		0.65	1.3	1.95	Ω		
Turn-On Delay Time	t _{d(on)}			14	25			
Rise Time	t _r	V_{DD} = 30 V, R_L = 30 Ω		12	20			
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong\text{1 A, V}_\text{GEN}=\text{10 V, R}_\text{g}=\text{6}\ \Omega$		50	80	ns		
Fall Time	t _f			12	20			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 3.2 A, di/dt = 100 A/μs		60	100			

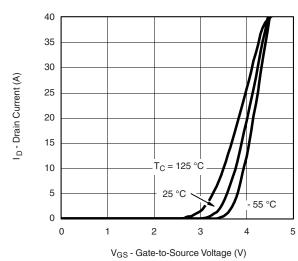
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





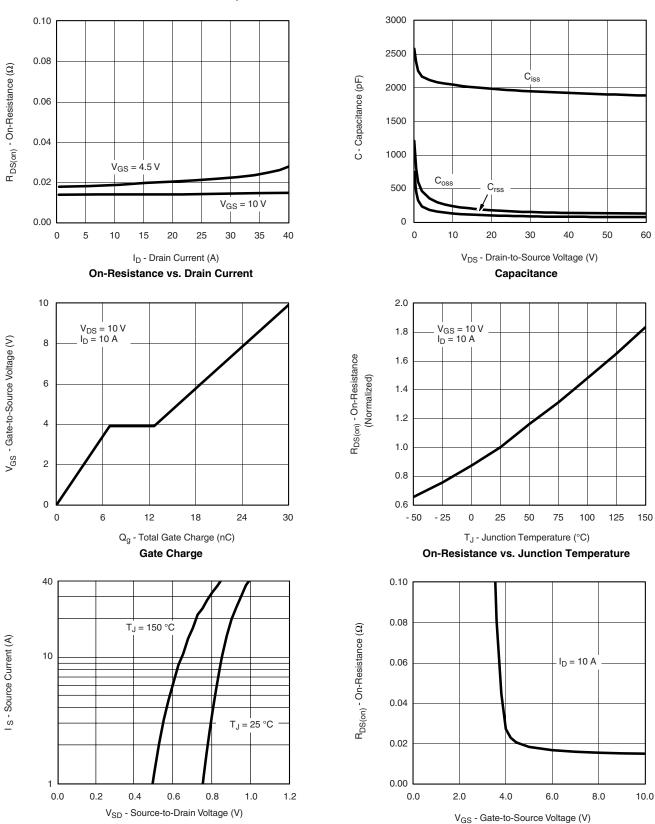
Transfer Characteristics







TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



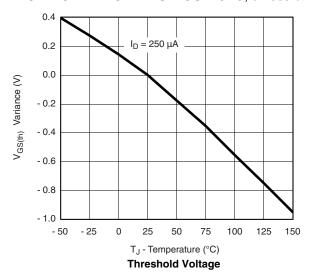
Source-Drain Diode Forward Voltage

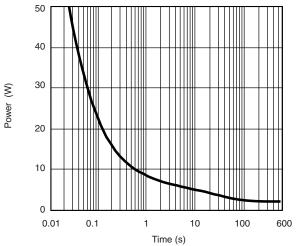
On-Resistance vs. Gate-to-Source Voltage

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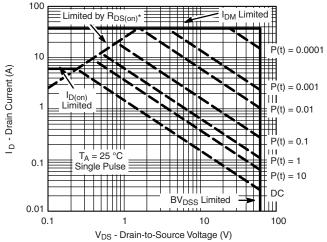
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



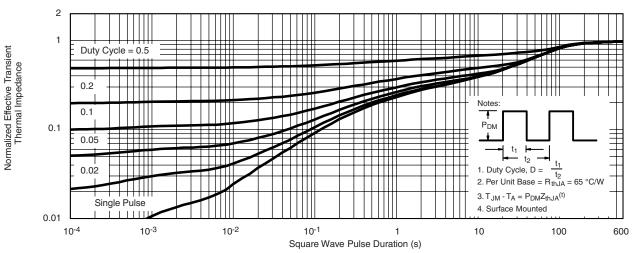


Single Pulse Power, Junction-to-Ambient



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

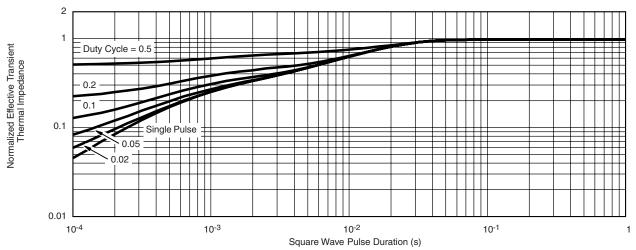
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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